



$\text{Bi}_{2-x}\text{Tl}_x\text{Te}_3$	2 - 4mm
Material properties	Topological insulator, thermoelectric
Crystal structure	Trigonal phase
Unit cell parameters	$a=b=0.431 \text{ nm}$ , $c = 3.052 \text{ nm}$ , $\alpha=\beta=90^\circ$ , $\gamma=120^\circ$ above parameters change with the TI (x) concentration
Growth method	Chemical vapor transport (CVT) technique
Purity	5.5N electronic grade [Confirmed and guaranteed at 99.9995%]